

## I CLAIM:

1. A semiconductor diode comprising:  
a semiconductor die including a substrate, a  
first semiconductor film formed on said substrate,  
5 a second semiconductor film formed on said first  
semiconductor film, a first metal contact formed on  
said first semiconductor film, and a second metal  
contact formed on said second semiconductor film, one  
of said first and second semiconductor films being  
10 made of an n-type semiconductor material, the other  
one of said first and second semiconductor films being  
made of a p-type semiconductor material, said  
semiconductor die having two opposing first side  
edges and two opposing second side edges which  
15 cooperates with said first side edges to define  
thereamong two diagonally opposite first corners and  
two diagonally opposite second corners, said first  
semiconductor film having an exposed area that is  
exposed from said second semiconductor film adjacent  
20 to one of said first side edges and that extends  
between one of said first corners and one of said  
second corners, said first metal contact having a  
first strip portion that is formed on said exposed  
area , and a first bonding portion that extends from  
25 and that has a width greater than that of said first  
strip portion and a length less than that of said first  
strip portion, said second metal contact having a

second strip portion that is disposed adjacent to the other one of said first side edges and that extends between the other one of said first corners and the other one of said second corners, and a second bonding portion that extends from and that has a width greater than that of said second strip portion and a length less than that of said second strip portion.

2. The semiconductor diode of Claim 1, wherein said first bonding portion is formed on said one of said 10 first corners, said first strip portion extending from said first bonding portion to said one of said second corners, said second bonding portion being formed on the other one of said first corners, said second strip portion extending from said second bonding portion to the other one of said second corners.

3. The semiconductor diode of Claim 1, further comprising a quantum well sandwiched between said first and second semiconductor films.

20 4. The semiconductor diode of Claim 1, further comprising an ohmic metal contacting film sandwiched between said second semiconductor film and said second metal contact.

5. The semiconductor diode of Claim 4, further 25 comprising a dielectric film sandwiched between said second metal contact and said metal contacting film, said dielectric film having a geometric dimension

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less than that of said second metal contact such that said second metal contact is in electrical contact with said metal contacting film.

6. The semiconductor diode of Claim 1, wherein said  
5 substrate is made of a material selected from a group  
consisting of sapphire and silicon carbide.

7. The semiconductor diode of Claim 1, wherein said  
n-type semiconductor material is n-doped GaN material,  
and said p-type semiconductor material is p-doped GaN  
10 material.

8. A method for manufacturing semiconductor diodes,  
comprising the steps of:

preparing a substrate;  
forming a first semiconductor film on said  
15 substrate;

forming a second semiconductor film on said  
first semiconductor film, wherein one of said first  
and second semiconductor films is made of an n-type  
semiconductor material, and the other one of said  
20 first and second semiconductor films is made of a  
p-type semiconductor material;

selectively masking and etching said second  
semiconductor film to define a plurality of orderly  
arranged exposed areas on said first semiconductor  
25 film which are exposed from said second semiconductor  
film;

forming a plurality of orderly arranged first

metal contacts on said exposed areas of said first semiconductor film, respectively, and a plurality of second metal contacts on said second semiconductor film, each of said second metal contacts being  
5 associated with a respective one of said first metal contacts; and

dicing assembly of said substrate, said first semiconductor film, said second semiconductor film, said first metal contacts, and said second metal  
10 contacts to form a plurality of semiconductor dies, each of which has two opposing first side edges and two opposing second side edges which cooperates with said first side edges to define thereamong two diagonally opposite first corners and two diagonally  
15 opposite second corners;

wherein, said exposed area on said first semiconductor film of each of said semiconductor dies is disposed adjacent to one of said first side edges and extends between one of said first corners and one  
20 of said second corners, said first metal contact of each of said semiconductor dies having a first strip portion that is formed on said exposed area, and a first bonding portion that extends from and that has a width greater than that of said first strip portion  
25 and a length less than that of said first strip portion, said second metal contact of each of said semiconductor dies being disposed adjacent to the

other one of said first side edges and having a second strip portion that extends between the other one of said first corners and the other one of said second corners, and a second bonding portion that extends 5 from and that has a width greater than that of said second strip portion and a length less than that of said second strip portion.

9. The method of Claim 8, wherein said first bonding portion is formed on said one of said first corners, 10 said first strip portion extending from said first bonding portion to said one of said second corners, said second bonding portion being formed on the other one of said first corners, said second strip portion extending from said second bonding portion to the 15 other one of said second corners.

10. The method of Claim 8, further comprising a step of forming a quantum well on said first semiconductor film prior to the formation of said second semiconductor film on said first semiconductor film.

20 11. The method of Claim 8, further comprising a step of forming an ohmic metal contacting film on said second semiconductor film prior to the formation of said second metal contact on said second semiconductor film.

25 12. The method of Claim 11, further comprising a step of forming a dielectric film on said metal contacting film, said second metal contact being formed on said

dielectric film which has a geometric dimension less than that of said second metal contact such that said second metal contact is in electrical contact with said metal contacting film.

5 13. The method of Claim 8, wherein said substrate is made of a material selected from a group consisting of sapphire and silicon carbide.

14. The method of Claim 8, wherein said n-type semiconductor material is n-doped GaN material, and  
10 said p-type semiconductor material is p-doped GaN material.